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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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PRODUCTION DATA SHEET

DESCRIPTION

The LX5560 is a low noise amplifier HEMT (E-pHEMT) process.

It operates with a single positive variation compared to a voltage supply of 3.3V, with noise resistor-network bias circuit. figure(NF) of 1.7dB while maintaining input third order intercept point(IIP3) of up to +6dBm.

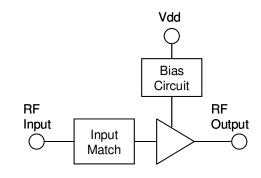
The LNA is implemented with bias (LNA) for WLAN applications in the circuit and input matching circuit on 4.9-6.0 GHz frequency range. This chip, resulting in simple external LNA is manufactured with an InGaAs circuit. In addition, the on-chip bias Enhancement mode pseudomorphic circuit provides stable performance of gain, NF and current for voltage

> The LX5560 is available in a 12-pin 2mmx2mm micro-lead package(MLPQ-12L).

KEY FEATURES

- 0.5µm InGaAs E-mode pHEMT
 - 4.9 6GHz Operation
- Single 3.3V Supply
- Gain ~ 12dB
- Noise Figure ~ 1.7dB
- Input IP3 ~ +6dBm
- Input P1dB ~ +2dBm
- On-Chip Bias Circuit
- On-Chip Input Match
- Simple Output Match
- 2x2mm² MLPQ 12 Pin
- Low Profile 0.5mm

BLOCK DIAGRAM

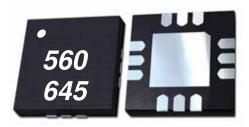


IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

APPLICATIONS

- Wireless LAN 802.11a
- WiMax

PRODUCT HIGHLIGHT



PACKAGE ORDER INFO **Plastic MLPQ** 12 pin RoHS Compliant / Pb-free LX5560LL

Note: Available in Tape & Reel. Append the letters TR" to the part number. (i.e. LX5560LL-TR)



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ABSOLUTE MAXIMUM RATINGS

DC Supply Voltage, RF Off	4 V
Drain Current	
Total Power Dissipation	0.15 W
RF Input Power	+10 dBm
Operation Ambient Temperature Range	40°C to +85°C
Storage Temperature Range	65°C to 150°C
Package Peak Temp. for Solder Reflow (40 seconds maximum expos	ure) 260°C (+0 -5)

Note: Exceeding these ratings could cause damage to the device. All voltages are with respect to Ground. Currents are positive into, negative out of specified terminal.

RoHS / Pb-free NiPdAu Lead Finish

FUNCTIONAL PIN DESCRIPTION			
Name	me Pin # Description		
RF IN	2	RF Input for the low noise amplifier. This pin is DC-shorted to GND but AC-coupled to the transistor gate.	
RF OUT	8	RF Output for the low noise amplifier. This pin is AC-coupled and does not require a DC-blocking capacitor.	
VDD	12	Supply Voltage.	
GND	Center Metal	The center metal base of the MLP package provides both DC and RF ground.	
N/C	1,3,4,5,6,7, 9,10,11	Not Used. They may be treated either as open pins or connected to the ground.	



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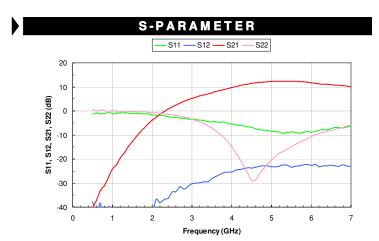
ELECTRICAL CHARACTERISTICS

Nominal test conditions: $V_{DD} = 3.3V$, $I_{DD} = 9.5mA$, $T_A = 25$ °C (Room Temperature)

Parameter	Symbol	Test Conditions	LX5560			Units
Farameter	Symbol	iliboi l'est collutions		Тур	Max	Units
Application Frequency Range	f		4.9		6	GHz
Small-Signal Gain	S21			12		dB
Noise Figure	NF	Room Temperature		1.7	2.1	dB
Input 3 rd Order Intercept Point	IIP3	Freq. 1 = 5.25 GHz, Freq. 2 = 5.27 GHz		6		dBm
Input P1dB	IP1dB	Freq. = 5.5 GHz		2		dBm
Input Return Loss	S11			9		dB
Output Return Loss	S22			10		dB
Supply Voltage	V_{DD}			3.3		V
Supply Current	I_{DD}			9.5		mA



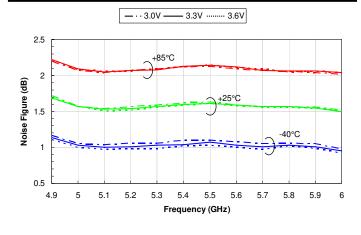
PRODUCTION DATA SHEET



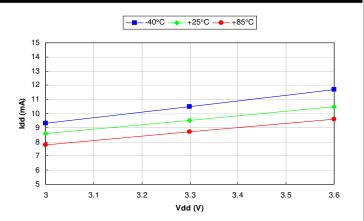
Typical S-Parameter Data at Room Temperature (Vdd = 3.3V, Idd = 9.5mA at Room Temperature)

GAIN OVER TEMP - - 3.0V 3.3V 3.6V 15 14 -40°C 13 S21 (dB) +25°C 11 +85°C 10 5 5.1 5.2 6 4.9 5.3 5.4 5.5 5.6 5.8 5.9 Frequency (GHz)

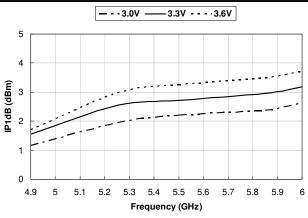
NOISE FIGURE OVER TEMP



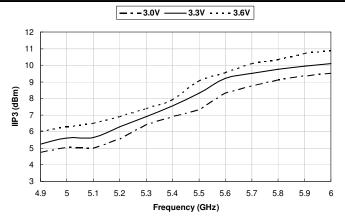
CURRENT OVER TEMP



INPUT P1DB (+25°C)



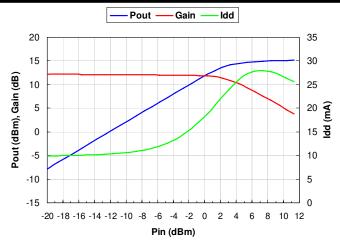
INPUT IP3 (+25°C)





PRODUCTION DATA SHEET

POWER SWEEP @ 5.5GHz

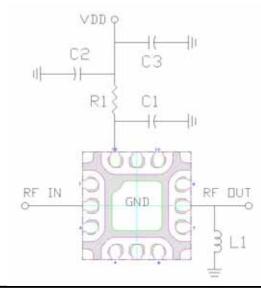


(Vdd=3.3V, Idq=9.5mA at Room Temperature)



PRODUCTION DATA SHEET

APPLICATION SCHEMATIC



BOM LIST				
Reference Designator	Reference Designator Part Description			
C1	Capacitor, 1 pF	0402		
C2	Capacitor,1 μF	0603		
C3	Capacitor,10 μF	0805		
L1	Inductor, 1.5 nH (TOKO: LL1005-FH1N5S)	0402		
R1	Resistor, 30 Ohm	0402		

NOTES

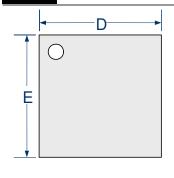
- It is recommended to place C1 at ~30mil from MLP package outline.
- It is recommended to place L1 at ~30mil from MLP package outline.
- C2 and C3 are used for standalone evaluation board test only. They can be replaced with a 1nF(0402) in final applications.

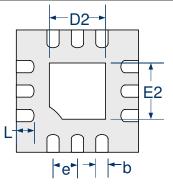


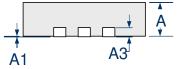
PRODUCTION DATA SHEET

PACKAGE DIMENSIONS

12-Pin MLPQ Plastic (2x2mm)



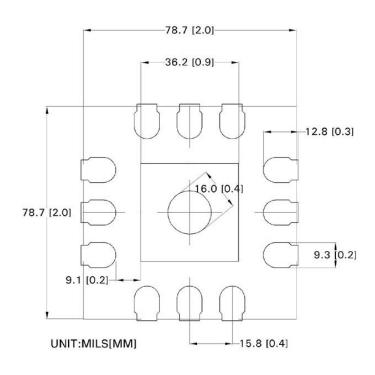




	MILLIMETERS		INCHES	
Dim	MIN	MAX	MIN	MAX
Α	0.40	0.50	0.016	0.020
A1	0.00	0.05	0.000	0.002
A3	0.15 REF		0.006 REF	
b	0.15	0.25	0.006	0.010
D	2.00 BSC		0.079 BSC	
D2	0.77	1.02	0.030	0.040
Е	2.00 BSC		0.079	BSC
E2	0.77	1.02	0.030	0.040
е	0.40 BSC		0.016 BSC	
L	0.19	0.39	0.007	0.015

Note:

 Dimensions do not include mold flash or protrusions; these shall not exceed 0.155mm(.006") on any side. Lead dimension shall not include solder coverage.



Recommended Land Pattern



LX5560

InGaAs - E-Mode pHEMT Low Noise Amplifier

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NOTES

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